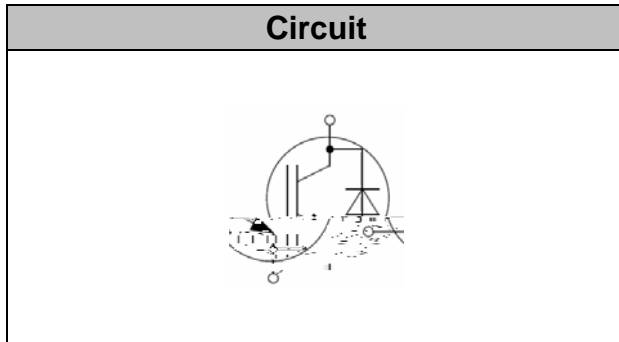


IGBT Discrete

V_{CE}	1200	V
I_C	25	A
$V_{CE(SAT)}$ $I_C=25A$	1.85	V



Applications

-
-
-

Features

-
-
-
-

Maximum Ratings

Parameter	Symbol	Value	Unit



DGW25N120CTL

Electrical Characteristics of the IGBT

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						



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Electrical Characteristics of the Diode

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at $T_j= 25$						
Dynamic , at $T_j= 125$						
Dynamic , at $T_j= 150$						



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Electrical Characteristics of the DIODE

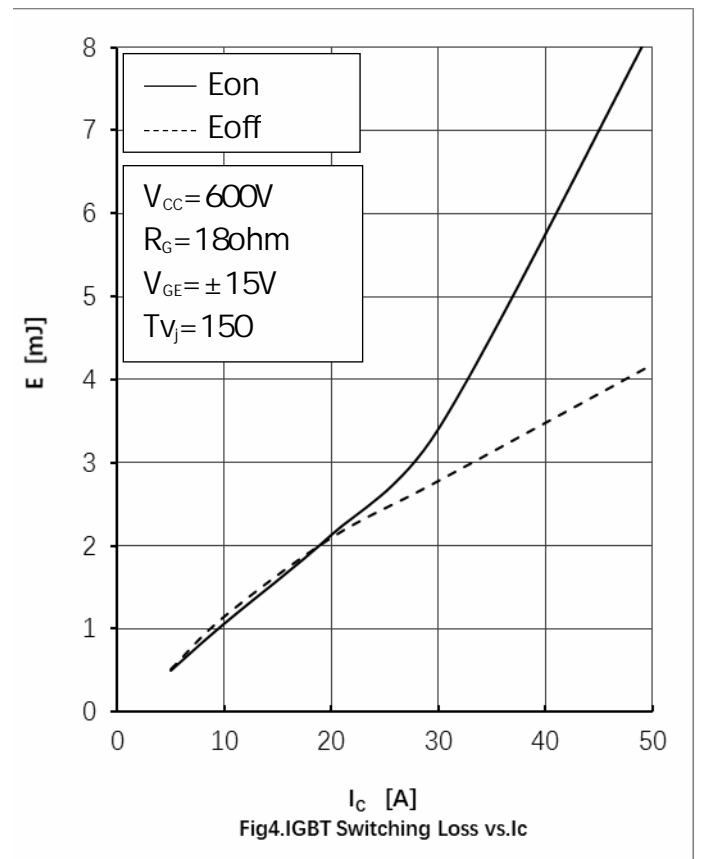
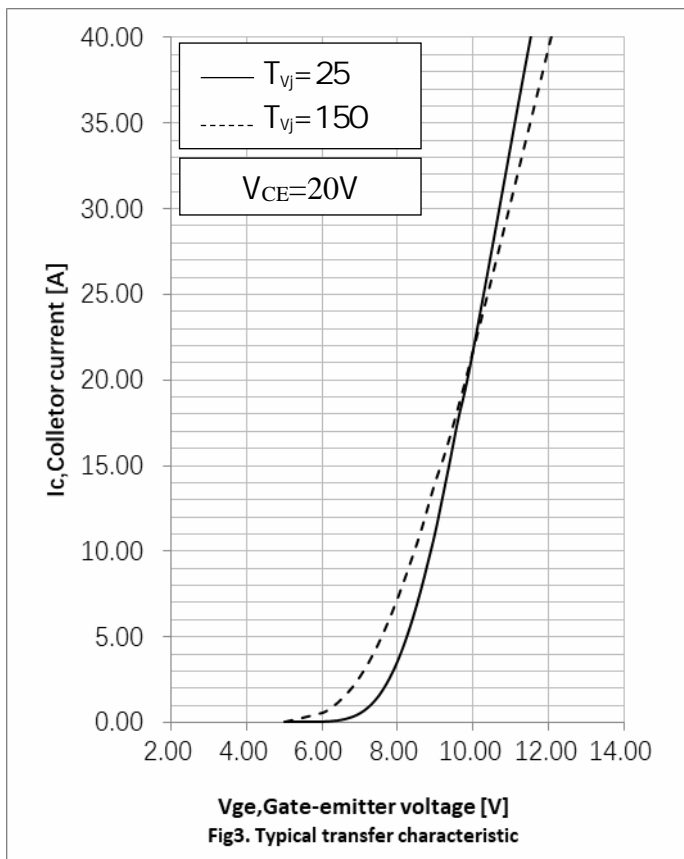
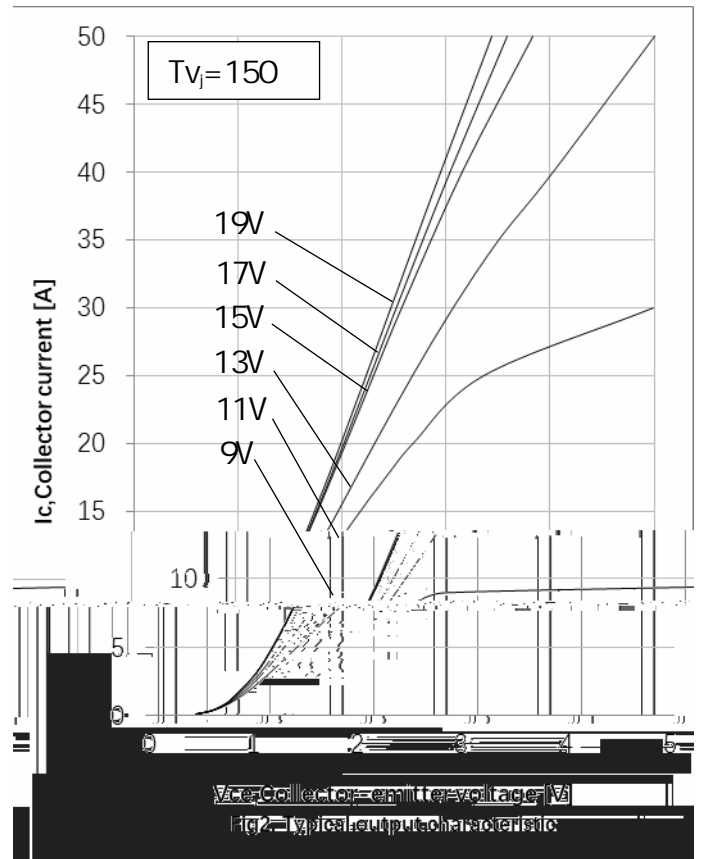
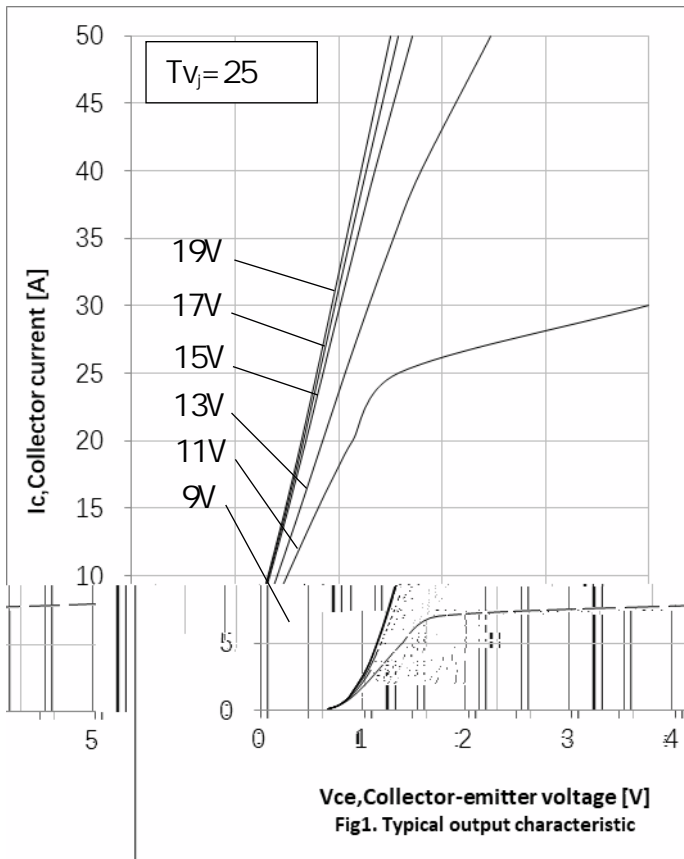
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Dynamic , at T_j= 125						
Dynamic , at T_j= 150						

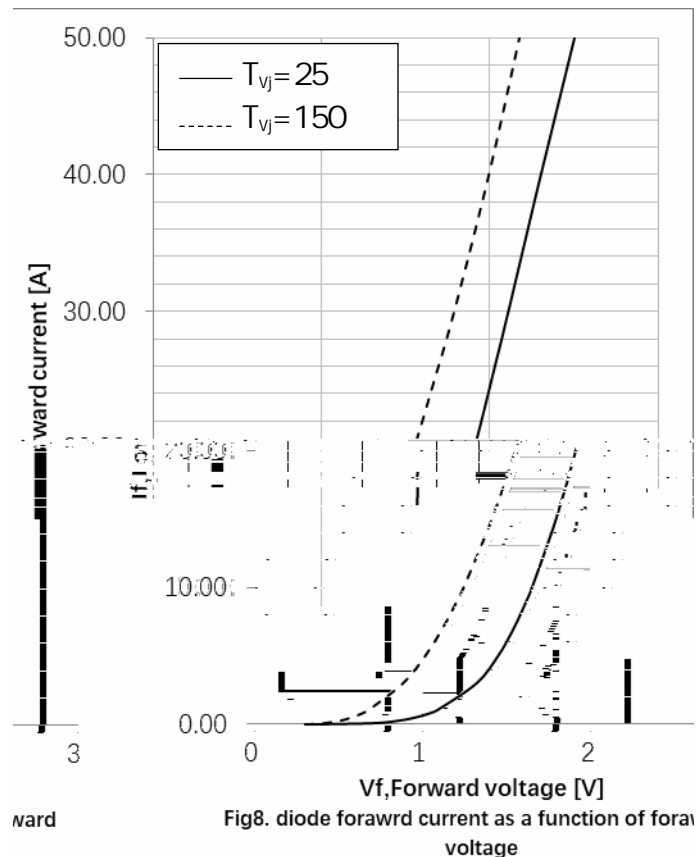
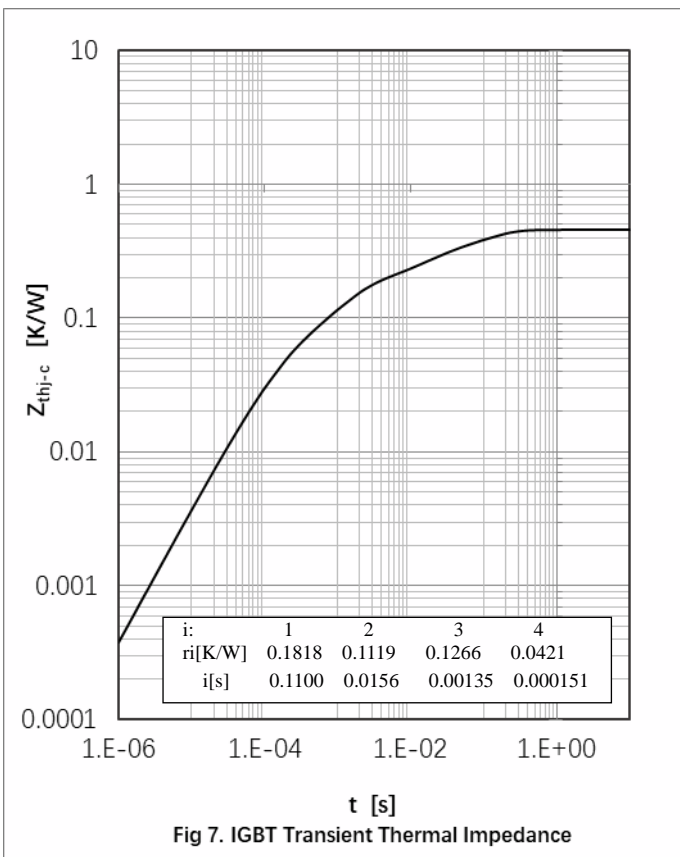
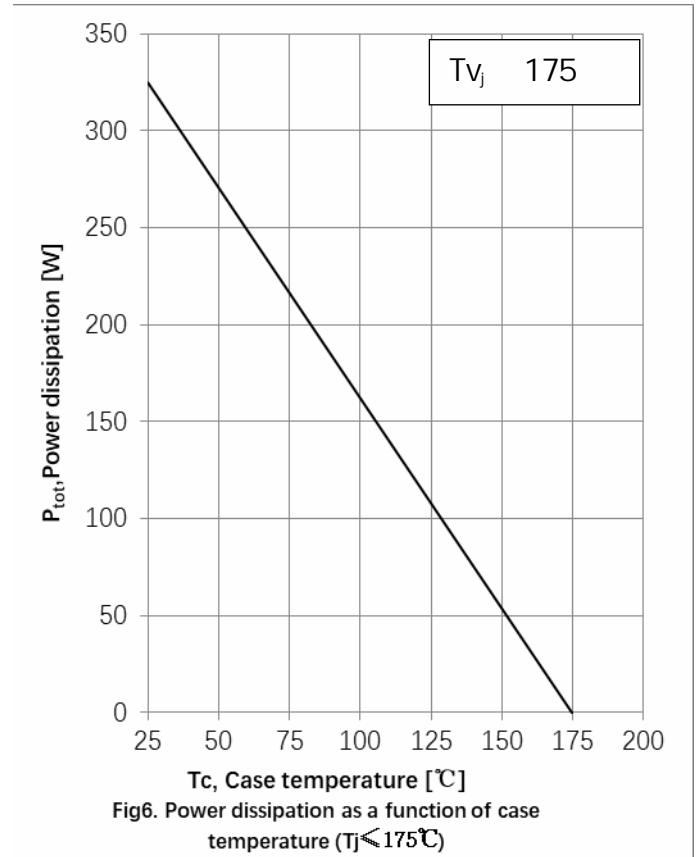
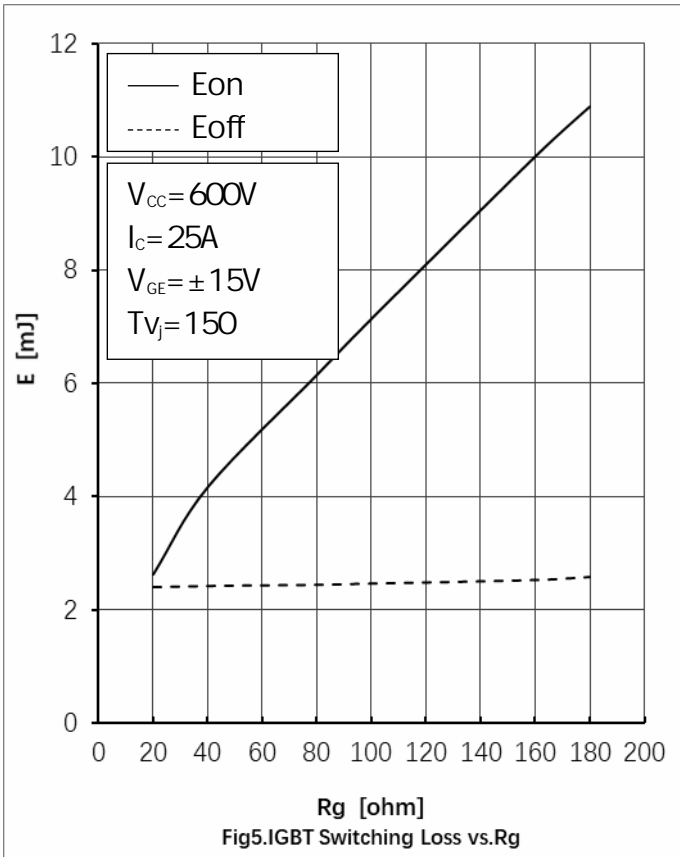
Thermal Resistance

Parameter	Symbol	Max. Value	Unit



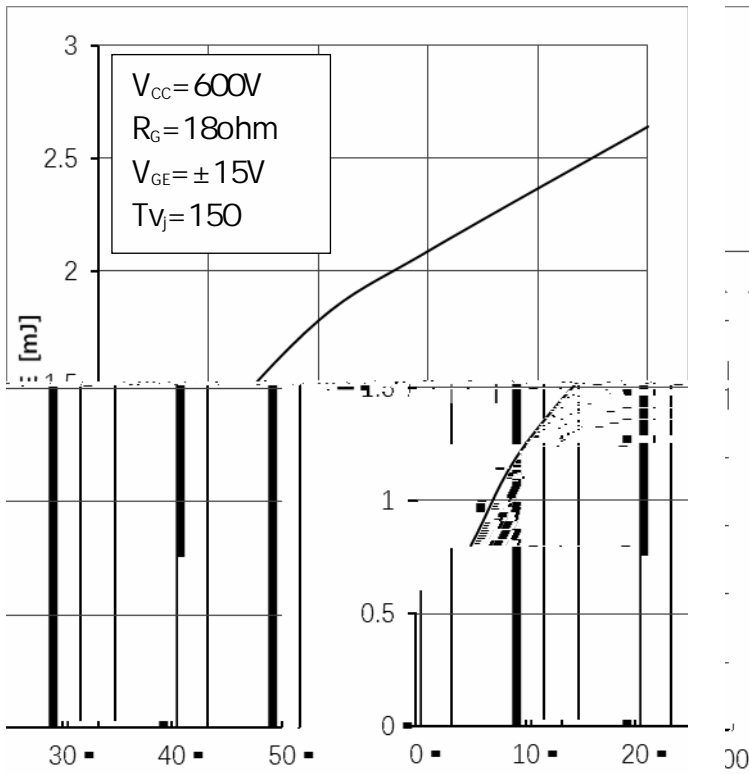
DGW25N120CTL



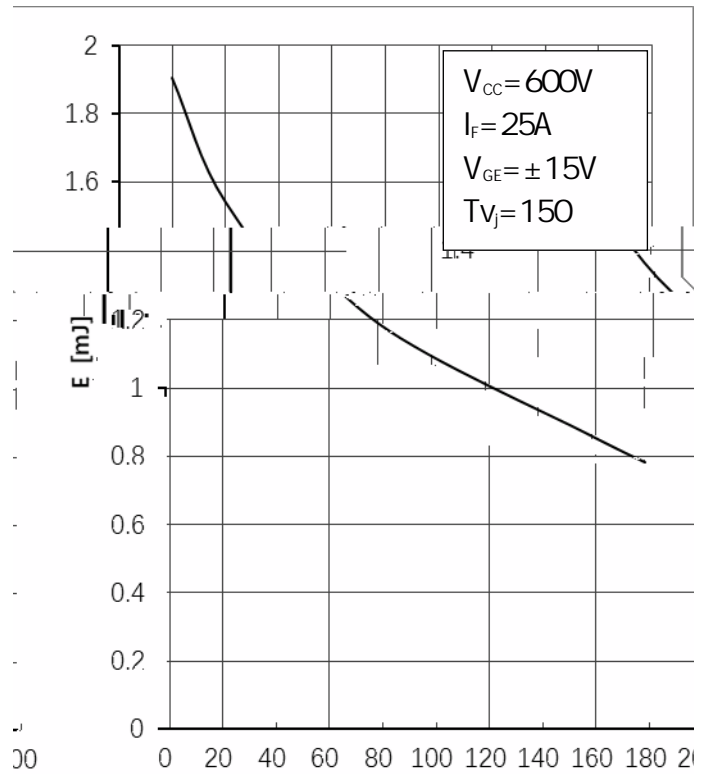




DGW25N120CTL



a) I_F [A]
Fig9. Diode Switching Loss (Erec) vs. I_F



R_G [ohm]
Fig10. Diode Switching Loss (Erec) vs. R_G

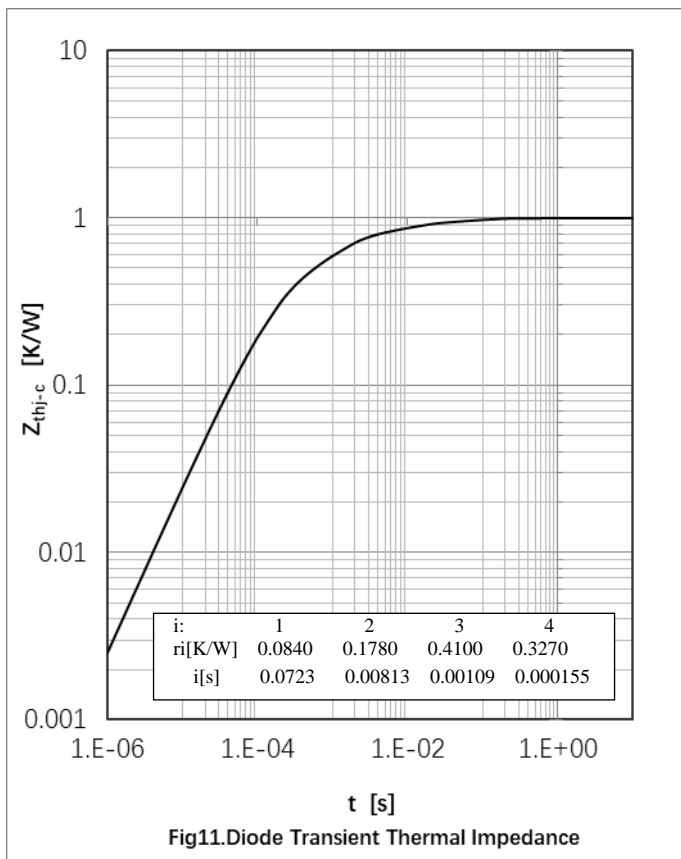


Fig11. Diode Transient Thermal Impedance

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Circuit Diagram

Package Outline Information

CASE: TO 247